



NASA Standards Update:

Electrical, Electronic, Electromechanical, and Electro-optical (EEEE or Quad-E) Parts Selection, Testing and Derating Standard (NASA-STD-8739.11)

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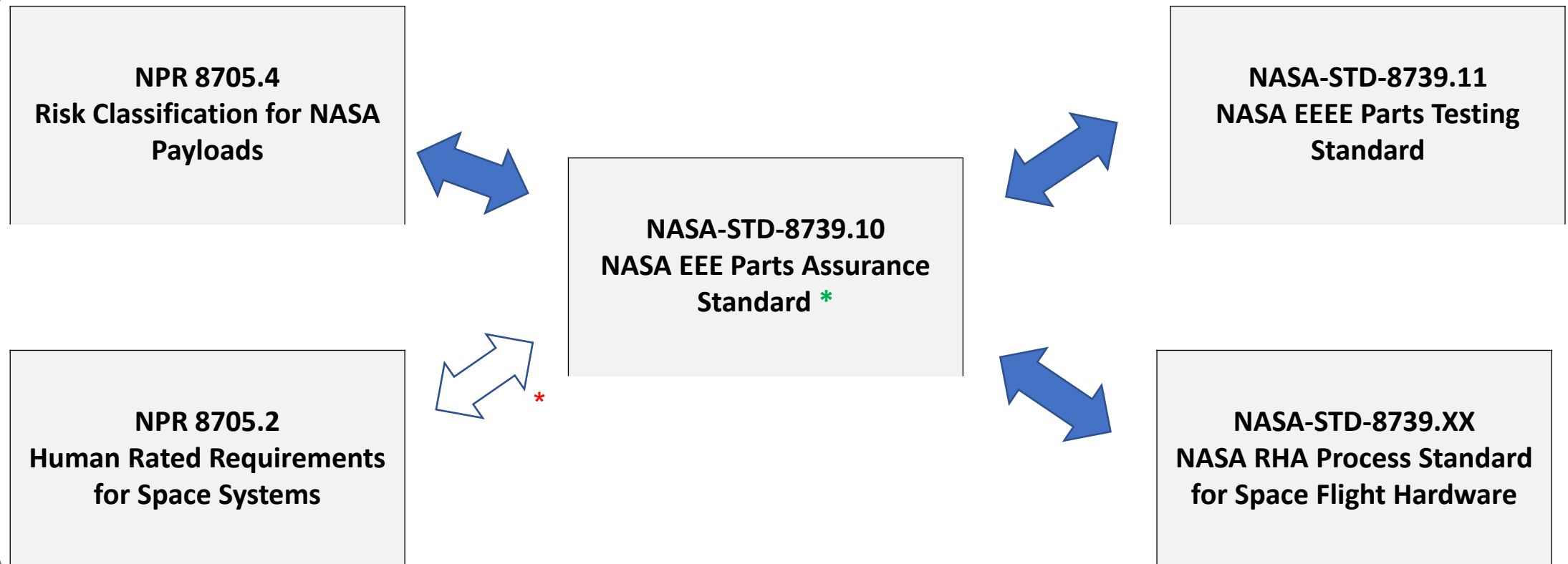
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Policy / Guidance



** Not a direct reference*

** Revision planned for FY25*



NASA Engineering and Safety Center Recommendations on the Use of COTS EEE Parts for NASA Missions

NASA/TM-20220018183
NESC-RP-19-01490



Recommendations on the Use of Commercial-Off-The-Shelf (COTS) Electrical, Electronic, and Electromechanical (EEE) Parts for NASA Missions – *Phase II*

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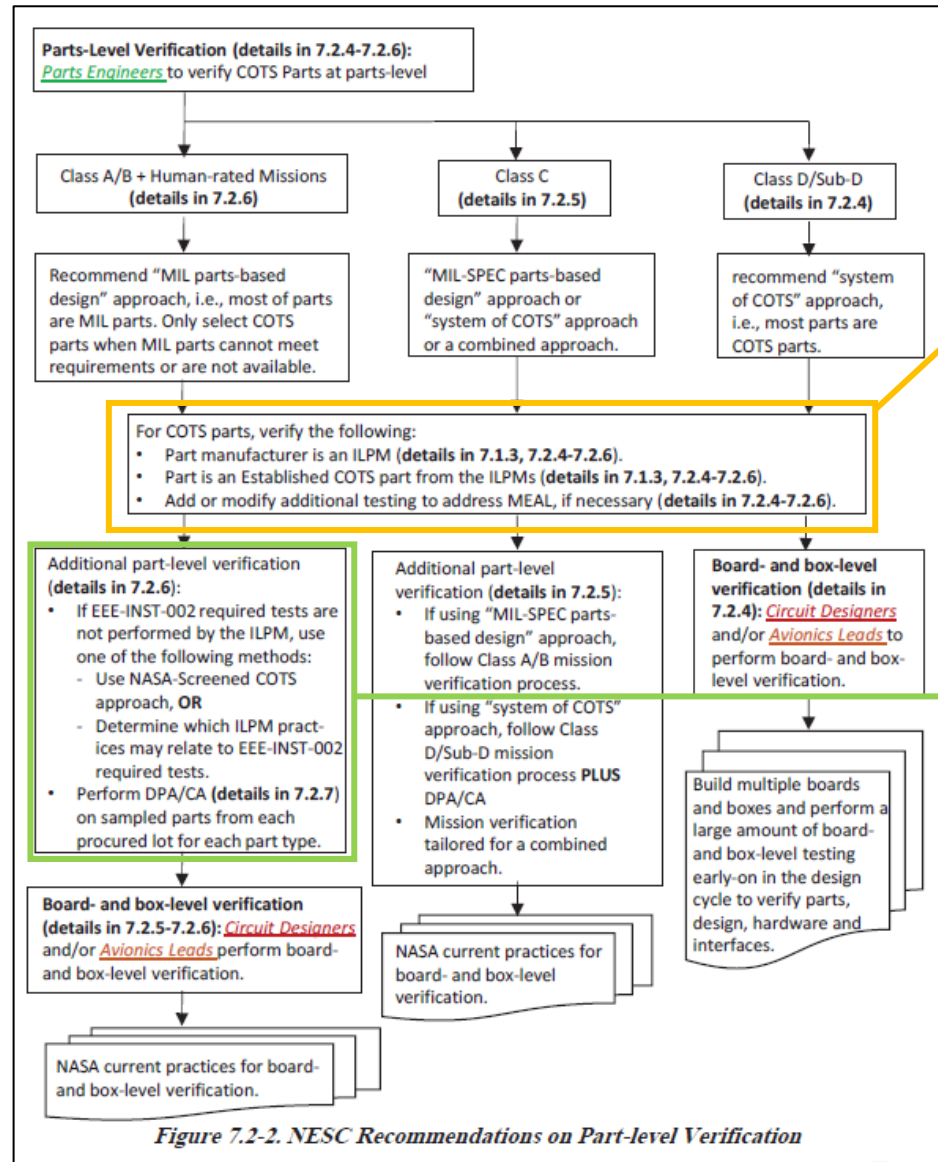
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December 2022

EEE Parts Assessment Flow Using the ILPM Process



NEPP ILPM Pathfinder activities are targeted here.

For COTS parts, verify the following:

- Part manufacturer is an ILPM (details in 7.1.3, 7.2.4-7.2.6).
- Part is an Established COTS part from the ILPMs (details in 7.1.3, 7.2.4-7.2.6).
- Add or modify additional testing to address MEAL, if necessary (details in 7.2.4-7.2.6).

Additional part-level verification (details in 7.2.6):

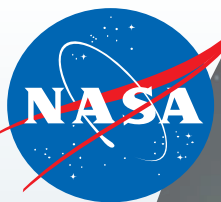
- If EEE-INST-002 required tests are not performed by the ILPM, use one of the following methods:
 - Use NASA-Screened COTS approach, **OR**
 - Determine which ILPM practices may relate to EEE-INST-002 required tests.
- Perform DPA/CA (details in 7.2.7) on sampled parts from each procured lot for each part type.

Implementation of ILPM Established COTS part usage in a mission is project-driven for now.
Executing at an agency-level is best.



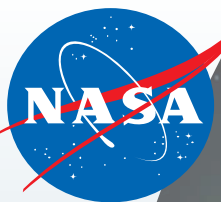
Electrical, Electronic, Electromechanical, and Electro-optical (EEEE or Quad-E) Parts Selection, Testing and Derating Standard

- Purpose:
 - Establishes a consistent set of requirements for selection, screening, lot acceptance testing, and derating of quad-E parts for use on NASA spaceflight projects.
 - Provides a mechanism to ensure that appropriate parts are used that will support mission reliability objectives within budget constraints.
- Does not attempt to adequately cover radiation effects of EEEE parts.



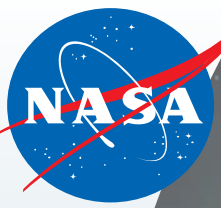
History

- Based on the EEE-INST-002, *Instructions for EEE Parts Selection, Screening, Qualification, and Derating*
 - GSFC document (used by other Centers)
 - 3 Quality Levels
 - 18 Device Specific Sections
 - Technology specific electrical testing (outdated)
 - Last update 2003
- Science Mission Directorate Policy: SMD Standard Mission Assurance Requirements For Payload Classification D
 - SMD encourages and empowers small mission project teams to take higher programmatic and technical risks when the potential for high scientific return at low cost has a fair likelihood of being achieved...
 - The Developer shall document and implement a Parts Control Plan. Per NASA-STD-8739.10, Level 4 or Commercial-Off-The-Shelf (COTS) parts may be used **without additional screening**.



NASA-STD-8739.11

- NASA Standard – Applicable to NASA Headquarters, Centers, JPL, contractors,... IAW contracts...
- 4 Assurance Levels
- 24 Device Specific Sections
- Includes MIL-Spec Plastic Encapsulated Classes
- Does not include technology specific electrical testing
- Lot Acceptance Testing vice Qualification
- No Screening Tests for AL 4
- No LAT Testing for AL 3 & 4



Sections (new in red)

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Review Comments: 849 Total

LIST OF SECTIONS

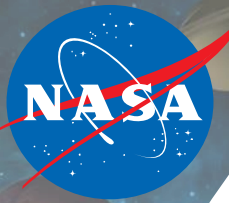
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Notes from comments adjudication

- Evident of meticulous review
- Not adding tests to raise “Class B” to “Class B+”
 - X-ray, PIND, NDBP
- Not limiting method of hermetic testing.
- Removed glass type capacitors
- Includes reference to ILPMs
- Wire and Cable Section in rewrite.
- Adding an option row for AEC-Q qualified devices for different data elements from manufacturer



Section M5 PEMs Table 1



Table 1. PLASTIC ENCAPSULATED MICROCIRCUIT REQUIREMENTS 1/

Assurance Level	Monolithic Microcircuit Type	Specification	Use as Is	Screening 4/	LAT 4/	DPA 4/
Level 1	QML Class P	MIL-PRF-38535				X
	QML Class N 2/	MIL-PRF-38535		X	X	X
	Automotive, Commercial, SCD 3/	AEC-Q100, VICD, SCD		X	X	X
Level 2	QML Class P or N	MIL-PRF-38535				X
	Automotive, Commercial, SCD 3/	AEC-Q100, VICD, SCD		X	X	X
Level 3	QML Class P or N	MIL-PRF-38535				X
	Automotive, Commercial, SCD 3/	AEC-Q100, VICD, SCD		X		X
Level 4	QML Class P or N	MIL-PRF-38535	X			
	Automotive, Commercial, SCD 3/	AEC-Q100, VICD, SCD	X			

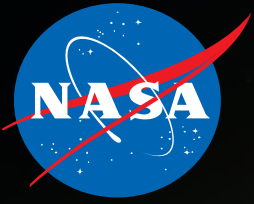


Section M5 PEMs Table 2



Table 2. PLASTIC ENCAPSULATED MICROCIRCUIT SCREENING 1/ 4/

	Test	Test Methods, Conditions, and Requirements	Level 1	Level 2	Level 3
1	Wafer Lot Acceptance	MIL-STD-883, Methods 5010 Appendix II and 5007	X		
2	Internal Visual	MIL-STD-883, Method 2010	X Cond. A		
3	Temperature Cycling	MIL-STD-883, 1010, Condition B, 10 Cycles min.	X	X	
4	External Visual	MIL-STD-883, 2009 (3 to 10X)	X	R	
5	PIND 2/	MIL-STD-883, 1010, Condition A	X	X	
6	Serialization		X	X	
7	Radiographic	PEM-INST-001 Para 5.3.2	X		
8	Burn-in 3/	MIL-STD-883, 1015, Condition D.	X 240 hr. @ 125 °C	X 160 hr. @ 125 °C	R 96 hr. @ 125 °C
9	Final Electrical Measurements at +25 °C, Min. and Max. Operating Temp.	Per applicable device procurement specification	X	X	X
10	Maximum Percent Defective Allowable (PDA)	Post Burn-in / Final Electrical Measurements @ 25 °C only	≤ 5%	≤ 10%	
11	External Visual	MIL-STD-883, 2009 (3 to 10X)	X	X	R



Questions?



4 Parts Assurance Levels

Assurance Level 1: The most stringent set of testing requirements; **typically aligns with the highest classes of MIL-SPEC space-grade parts (i.e., Class S)**. Requirements include screening, lot acceptance testing, DPA, and use of source control drawings for custom test flows.

Assurance Level 2: A substantial set of testing requirements; **typically aligns with the second-highest classes of MIL-SPEC parts (i.e., Class B)**. Requirements include screening, lot acceptance testing, and DPA, but with some tests, sample sizes, and durations **reduced from Assurance Level 1**. Use of source control drawings is encouraged, but not always required.

Assurance Level 3: Allows MIL-SPEC based designs and an infusion of commercial part-based designs with minimally burdensome piece-part testing requirements. **Generally, includes some screening, but does not impose lot acceptance testing**. Criteria rely heavily on DPA as an inexpensive test to obtain objective insight into manufacturer workmanship and quality.

Assurance Level 4: Use of commercial parts with **no additional screening** or qualification. In applications that have low tolerance for risk, it is essential to have detailed information about the manufacturer and part prior histories.



Example from EEE-INST-002



Table 1 MONOLITHIC INTEGRATED CIRCUIT REQUIREMENTS (Page 1 of 2) 1/

Part Designation	Use As Is	Screen To Requirements in Table 2 2/	Qualify To Requirements in Table 3 2/
Level 1: 1) Class V or Class S 2) Class Q or Class B 3) SCD 4) 883-Compliant or Class M 5/	X	X 3/, 4/, 5/ X 4/, 5/ X 4/, 5/, 6/	X X
Level 2: 1) Class V or Class S 2) Class Q or Class B 3) 883-Compliant or Class M 6/ 4) SCD 5) Mfr. Hi-Rel 7/ 6) Commercial	X	X 4/ X 4/, 8/ X 4/, 8/ X 4/, 8/ X 4/, 8/	X 9/ X 9/ X 9/ X 9/
Level 3: 1) Class V (or S) 2) Class Q (or B) 3) 883-Compliant or Class M 4/, 9/ 4) SCD 9/ 5) Mfr. Hi-Rel 10/ 6) Commercial 10/	X	X 4/ X 4/ X 8/ X 8/ X 8/	

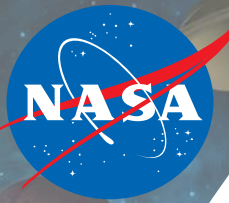
Notes follow on next page.



New Tables from 8739.11

Table 1. MONOLITHIC MICROCIRCUIT REQUIREMENTS 1/ 2/

Assurance Level	Monolithic Microcircuit Type	Specification	Use As Is	Screening	LAT	DPA
Level 1	QML Classes V, Y, S	MIL-PRF-38535	X			
	QML Classes; Q, B, 3/	MIL-PRF-38535		X 4/	X	
	All Types	SCD		X	X	X
Level 2	QML Classes V, Y, S	MIL-PRF-38535	X			
	QML Classes; Q, B, M	MIL-PRF-38535		X 4/		
	All Types	Automotive, Commercial, SCD		X	X	X
Level 3	QML Classes: V, Y, S	MIL-PRF-38535	X			
	QML Classes; Q, B, M	MIL-PRF-38535		R 4/		
	All Types	Automotive, Commercial, SCD		X		X
Level 4	QML Classes: V, Y, S, Q, B, M	MIL-PRF-38535	X			
	All Types	Automotive, Commercial, SCD	X			



New Tables from 8739.11



Table 1. PLASTIC ENCAPSULATED MICROCIRCUIT REQUIREMENTS 1/

Assurance Level	Monolithic Microcircuit Type	Specification	Use as Is	Screening 3/	LAT 3/	DPA 3/
Level 1	QML Class P	MIL-PRF-38535				X
	SCD 2/	SCD		X	X	X
Level 2	QML Class P or N	MIL-PRF-38535				X
	Automotive, Commercial, SCD 2/	AEC-Q100, VICD, SCD		X	X	X
Level 3	QML Class P or N	MIL-PRF-38535				X
	Automotive, Commercial, SCD 2/	AEC-Q100, VICD, SCD		X		X
Level 4	QML Class P or N	MIL-PRF-38535	X			
	Automotive, Commercial, SCD 2/	AEC-Q100, VICD, SCD	X			



New Tables from 8739.11

Table 2. MONOLITHIC MICROCIRCUITS SCREENING 1/

Test	Test Sequence	Test Methods, Conditions, and Requirements	Quality Level		
			Level 1	Level 2	Level 3
1	Wafer Lot Acceptance	MIL-STD-883, Methods 5010 Appendix II and 5007	X		
2	Nondestructive Bond Pull	MIL-STD-883, Method 2023, 2% PDA	X	X	
3	Internal Visual	MIL-STD-883, Method 2010	Condition A	Condition B	
4	Temperature Cycling	MIL-STD-883, Method 1010, Condition C, 10 Cycles min.	X	X	
5	Constant Acceleration	MIL-STD-883, Method 2001, Condition E, Y ₁ Orientation Only	X		
7	PIND	MIL-STD-883, Method 2020, Condition A	X	X	R
8	Serialization		X		
9	Radiographic 2/	MIL-STD-883, Method 2012, Two Views	X		
10.	Initial Electrical Measurements	Applicable device specification at +25°C	X	X	
11	Burn-in	MIL-STD-883, Method 1015, Condition C or D.	240 hrs	160 hrs	
12	Final Electrical Measurements	Applicable device specification at +25°C, Minimum, and Maximum Operating Temperatures	X	X	R
13	Calculate Delta	25°C Pre-Post Burn-in	X		
14	Calculate PDA	Pre-Post Burn-in 25°C DC Electrical 25°C Functional	5% 3%	10%	
15	Seal (Hermetic Types only) a. Fine Leak b. Gross Leak	MIL-STD-883, Method 1014 Condition CH or B (or A as Alternate) for Fine Leak Condition CH, B3, or C4 for Gross Leak	X X	X X	
16	External Visual	MIL-STD-883, Method 2009 (3X to 10X)	X	X	X

Notes:

- 1/ The character "X" designates a requirement. The character "R" designates a recommendation.
- 2/ Only one view is required for flat packages and leadless chip carriers having lead terminal metal on four sides.



New Tables from 8739.11



Table 3. MONOLITHIC MICROCIRCUITS LOT ACCEPTANCE TESTING 1/, 2/

Inspection/Test	Test Methods, Conditions, and Requirements	Quantity (Accept Number)	
		Level 1	Level 2
Group B			
Solderability	MIL-STD-883, Method 2003, Soldering temperature of 245 °C ± 5 °C, 3 samples min.	3(0) 22 leads(0)	3(0) 22 leads(0)
Group C			
Steady State Life Test	MIL-STD-883, Method 1005, Condition D, 1,000 hours at +125 °C	45(0) X	22(0) 3/ X
End-Point Electrical Parameters	Per applicable device procurement specification	X	X
Package Element Evaluation			
Subgroup 1			
Physical Dimensions	MIL-STD-883 Method 2016, Acquisition Document	3(0) X	3(0) X
Subgroup 2			
Visual Inspection	MIL-STD-883, Method 2009	100%	100%
Device Finish	Use a recognized methodology, verify all surface finishes are compliant with specification.	3(0)	3(0)
Subgroup 3			
Thermal Shock	MIL-STD-883, Method 1011	3(0) X	3(0) X
High Temperature Bake	MIL-STD-883, Method 1008	X	X
Lead Integrity	MIL-STD-883, Method 2004 Condition A1 (braze attached leads, 3 lead min.) Condition B1 (Rigid Leads and terminals only) Condition B2 (Lead Fatigue) Condition D (Pad adhesion of leadless chip carriers) Condition E (Plating integrity of flexible and semi-flexible lead, 3 leads min.) MIL-STD-883, Method 2028 for Pin grid array leads	X X X X X X X	X X X X X X X
Seal	MIL-STD-883, Method 1014 Condition A4 Unlidded cases	X	X
Subgroup 4			
Metal Package Isolation	MIL-STD-883 Method 1003, Condition E, 100nA max.	3(0) X	3(0) X
Subgroup 5			
Solderability	MIL-STD-883, Method 2003, Condition Soldering Temperature +245°C ±5°C	3(0)	3(0)